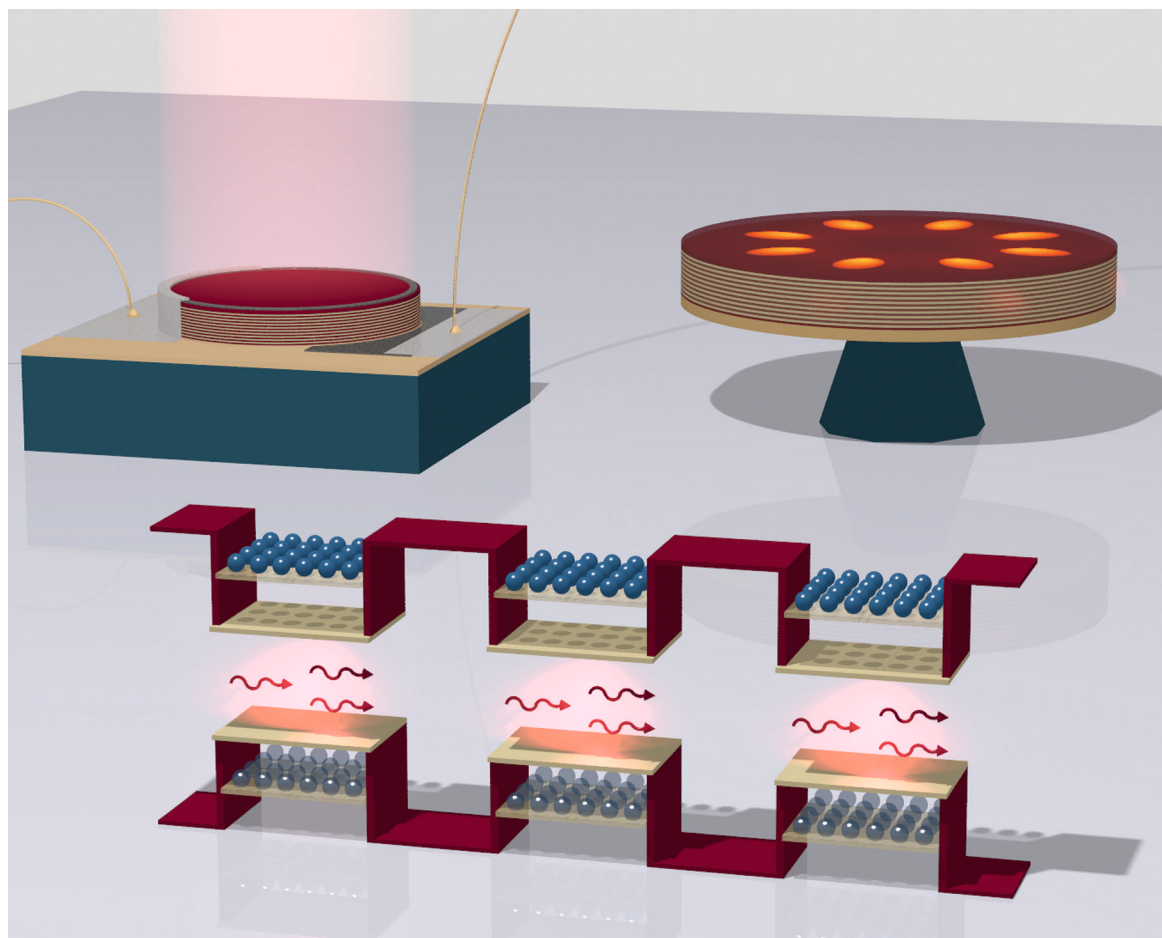




Group IV (Si)GeSn Light Emission and Lasing Studies

Daniela Stange

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Contents

1. Introduction	1
2. (Si)GeSn Material Properties	5
2.1. From Indirect to Direct Bandgap GeSn	6
2.1.1. Sn Incorporation	6
2.1.2. Strain Dependence	8
2.1.3. Si Incorporation	9
2.2. From Homojunction to Heterostructures	11
2.3. Radiative and Non-Radiative Recombination	13
3. Photoluminescence of GeSn Alloys	19
3.1. GeSn Single Layer	20
3.2. GeSn/SiGeSn Heterostructures	27
3.2.1. Material Overview	28
3.2.2. Light Emission	30
3.3. Summary	35
4. Light Emitting Diodes	37
4.1. Fabrication and Electrical Characterization	38
4.2. Homojunction LEDs	42
4.3. Heterostructure LEDs	47
4.3.1. Ge Barriers	48
4.3.2. SiGeSn Barriers	53
4.4. Summary	59

5. Optically Pumped Lasers	61
5.1. Laser Theory	63
5.2. Fabrication and Measurement Routine	68
5.3. GeSn Single Layer Lasers	69
5.3.1. Strain Distribution in Suspended Disk Structures	71
5.3.2. Lasing Characteristics	73
5.4. GeSn:P for Lasers	79
5.4.1. Material Overview	80
5.4.2. Lasing Characteristics	83
5.5. GeSn/SiGeSn Heterostructure Lasers	85
5.5.1. Strain and Band Structure in Undercut MQW Microdisks	86
5.5.2. Lasing Characteristics	89
5.6. Summary	96
6. Towards Electrically Pumped Lasing	99
7. Conclusion and Outlook	105
A. Appendix	111
Bibliography	113
Acknowledgments	143
List of Publications	147
Curriculum Vitae	153

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